

SOT-363 Plastic-Encapsulate Transistors

M MDT3904DW DUAL TRANSISTOR (NPN+NPN)

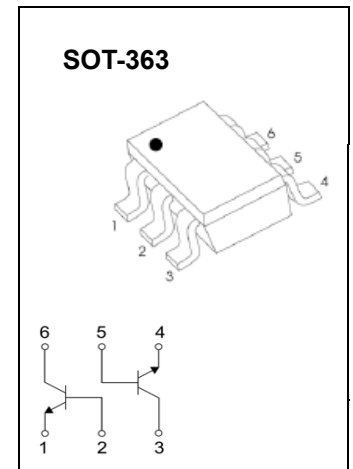
FEATURES

- Epitaxial planar die construction
- Ideal for low power amplification and switching

MARKING:K6N

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

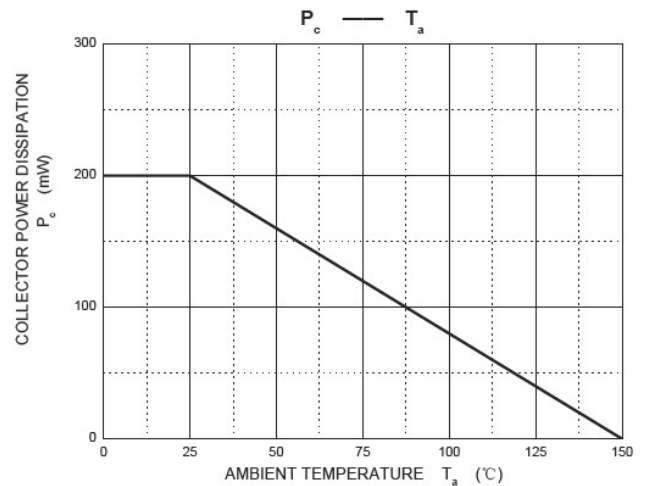
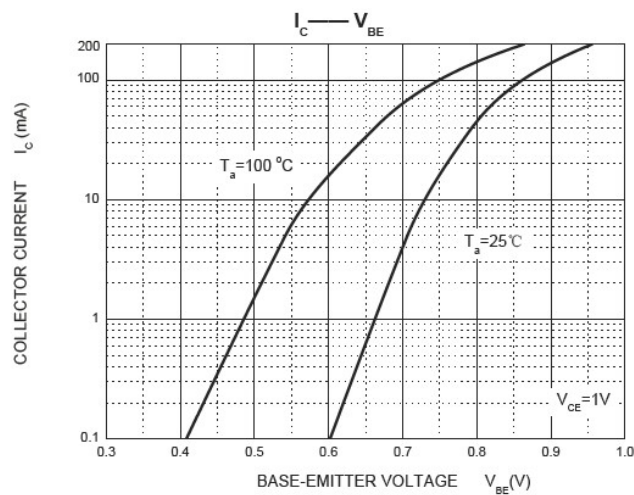
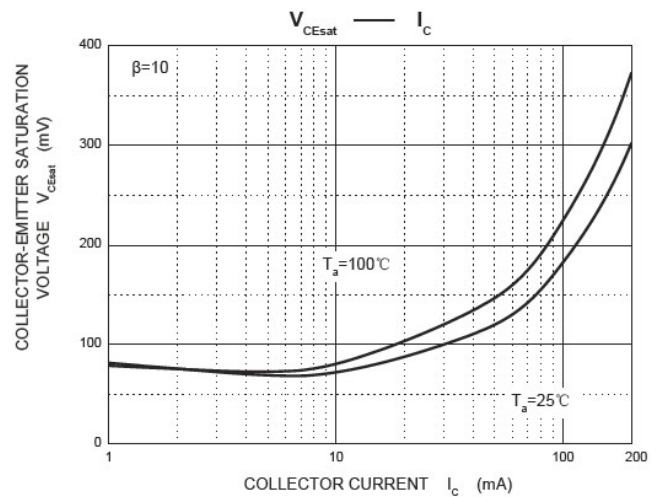
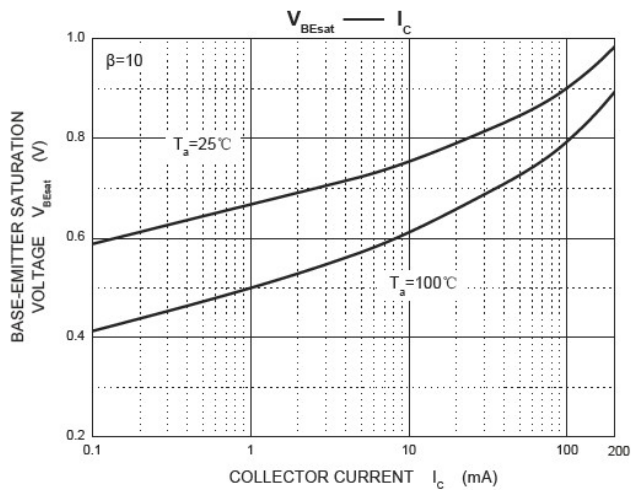
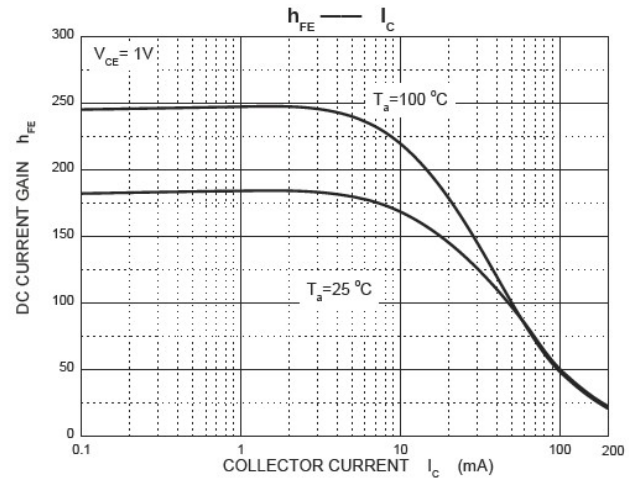
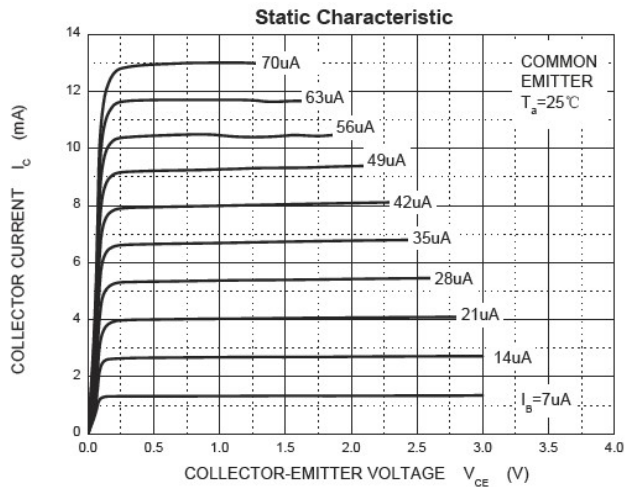
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Power Dissipation	0.2	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

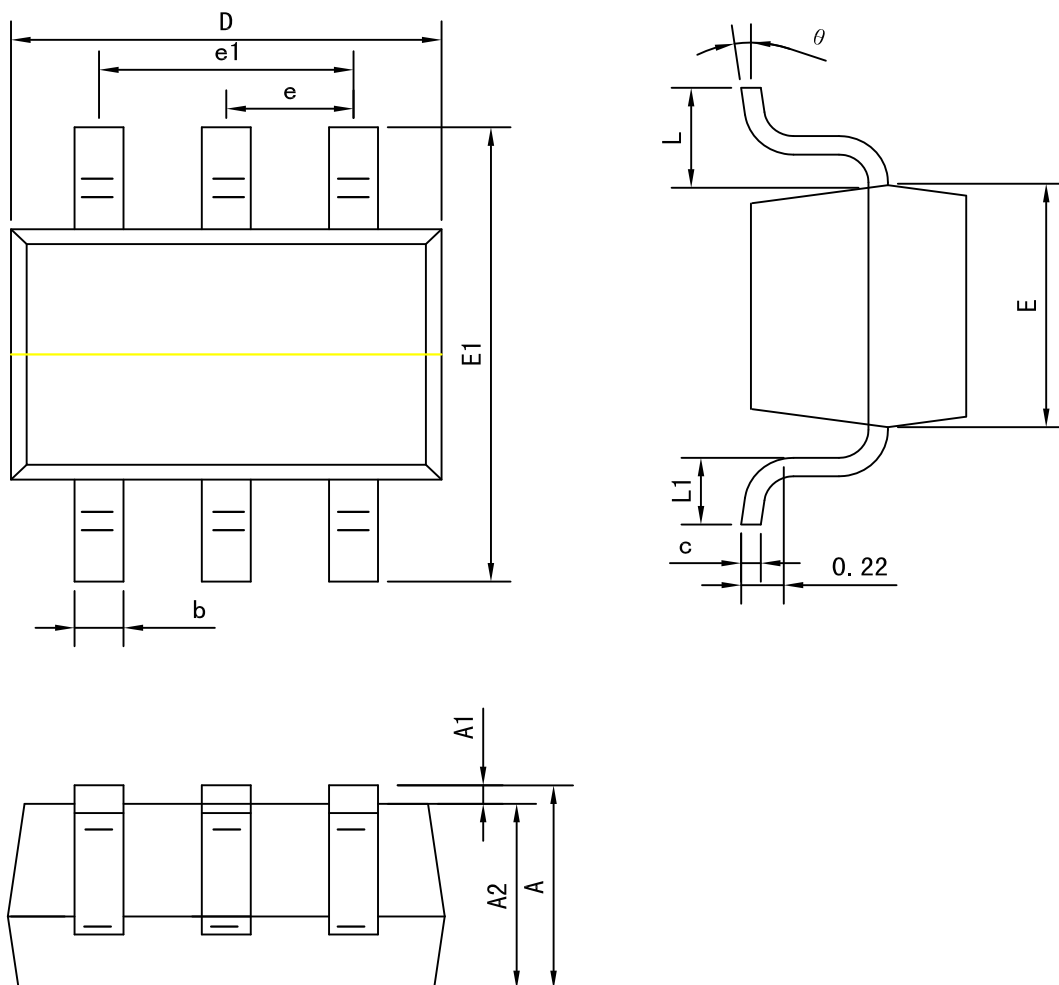
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.05	μA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{BE(off)}=3\text{V}$			0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
	$V_{CE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
	$V_{BE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz
Collector output capacitance	C_{ob}	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$			4	pF
Noise figure	NF	$V_{CE}=5\text{V}, I_C=0.1\text{mA}, f=1\text{kHz}, R_S=1\text{K}\Omega$			5	dB
Delay time	t_d	$V_{CC}=3\text{V}, V_{BE(off)}=-0.5\text{V}$			35	nS
Rise time	t_r	$I_C=10\text{mA}, I_{B1}=-I_{B2}=1\text{mA}$			35	nS
Storage time	t_s	$V_{CC}=3\text{V}, I_C=10\text{mA}$			200	nS
Fall time	t_f	$I_{B1}=-I_{B2}=1\text{mA}$			50	nS

Typical characteristics



Package outline dimensions

SOT-363



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.100	0.350
c	0.080	0.250
D	1.800	2.200
E	1.150	1.350
E1	2.000	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°